

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	(438/422,411,632,619,618,631,622.ccls. and (air adj gap)) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD")) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/07/12 13:55
S1	376	(438/618).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 12:46
S2	191	(438/619).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 12:36
S3	529	(438/622).CCLS.	USPAT; USOCR	OR	OFF	2005/10/20 07:31
S4	399	(438/631).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 13:54
S5	126	(438/632).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 12:27
S6	70	(438/411).CCLS.	USPAT; USOCR	OR	OFF	2006/01/28 13:48
S7	143	(438/421).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 12:01
S8	61	(438/422).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 11:34
S9	20	(257/527).CCLS.	USPAT; USOCR	OR	OFF	2006/01/31 08:50
S11	42317	"438"/\$.ccls.	USPAT	OR	OFF	2001/09/10 14:19
S14	52856	"257"/\$.ccls.	USPAT	OR	OFF	2005/04/04 13:08
S15	0	"438"/\$.ccls. with (air adj gap) and @ad<="20000724"	USPAT	OR	OFF	2005/04/04 13:10
S16	0	"257"/\$.ccls. with (air adj gap) and @ad<="20000724"	USPAT	OR	OFF	2005/04/04 13:10
S17	0	("257"/\$.ccls. same (air adj gap)) and @ad<="20000724"	USPAT	OR	OFF	2005/04/04 13:10
S18	0	("438"/\$.ccls. same (air adj gap)) and @ad<="20000724"	USPAT	OR	OFF	2005/04/04 13:10
S19	0	("438"/\$.ccls. with (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:11

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S20	0	("257"/\$.ccls. with (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:11
S21	0	("257"/\$.ccls. same (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:11
S22	0	("438"/\$.ccls. same (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:11
S23	484	("438"/\$.ccls. and (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:13
S24	4075	(semiconductor and (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:12
S25	544	(semiconductor and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:12
S26	157	("438"/\$.ccls. and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:17
S27	241	("257"/\$.ccls. and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:47
S28	61	(438/422,411,632,619,618,631, 622.ccls. and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:53

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S29	2	(438/422,411,632,619,618,631,622.ccls. and (air adj gap)) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD")) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/07/12 09:52
S30	136	(438/411).CCLS.	USPAT; USOCR	OR	OFF	2005/10/20 07:31
S31	2	(438/422,411,632,619,618,631,622.ccls. and (air adj gap)) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD")) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/28 13:47
S32	27	semiconductor and (air adj gap) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD")) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:45
S33	0	(semiconductor and (air adj gap) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD"))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/28 13:46
S34	0	(semiconductor and (air adj gap) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD"))).clm.	US-PGPUB	OR	OFF	2006/01/28 13:46
S35	30	(257/527).CCLS.	USPAT; USOCR	OR	OFF	2006/01/28 13:47
S36	172	(438/411).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:48
S37	392	(438/421).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:49

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S38	180	(438/359).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:49
S39	897	(438/404).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:49
S40	250	(438/456).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:50
S41	414	(438/619).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:50
S44	27	semiconductor and (air adj gap) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD")) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:45
S45	61	(438/422,411,632,619,618,631,622.ccls. and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:46
S46	61	(438/422,411,632,619,618,631,622.ccls. and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:53
S47	3	((("20040160118") or ("6718764") or ("20040126254"))).PN.	US-PGPUB; USPAT	OR	OFF	2006/01/31 08:51
S48	2	(438/422,411,632,619,618,631,622.ccls. and (air adj gap)) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD")) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/07/12 13:55

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S49	4	(("6200900") or ("6162723") or ("6077767") or ("5924006")).PN.	USPAT	OR	OFF	2006/07/12 09:53
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